

Product Summary

- $V_{DS} = -20V, I_D = -4A$
 $R_{DS(ON)} < 36m\Omega @ V_{GS} = -4.5V$
 $R_{DS(ON)} < 49m\Omega @ V_{GS} = -2.5V$
ESD Rating: 2500V HBM

Application

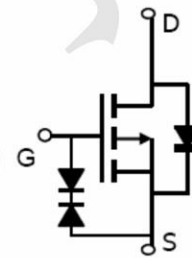
- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Package and Pin Configuration

SOT-23



Circuit diagram



Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous	I_D	-4	A
Drain Current-Pulsed (Note 1)	I_{DM}	-30	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

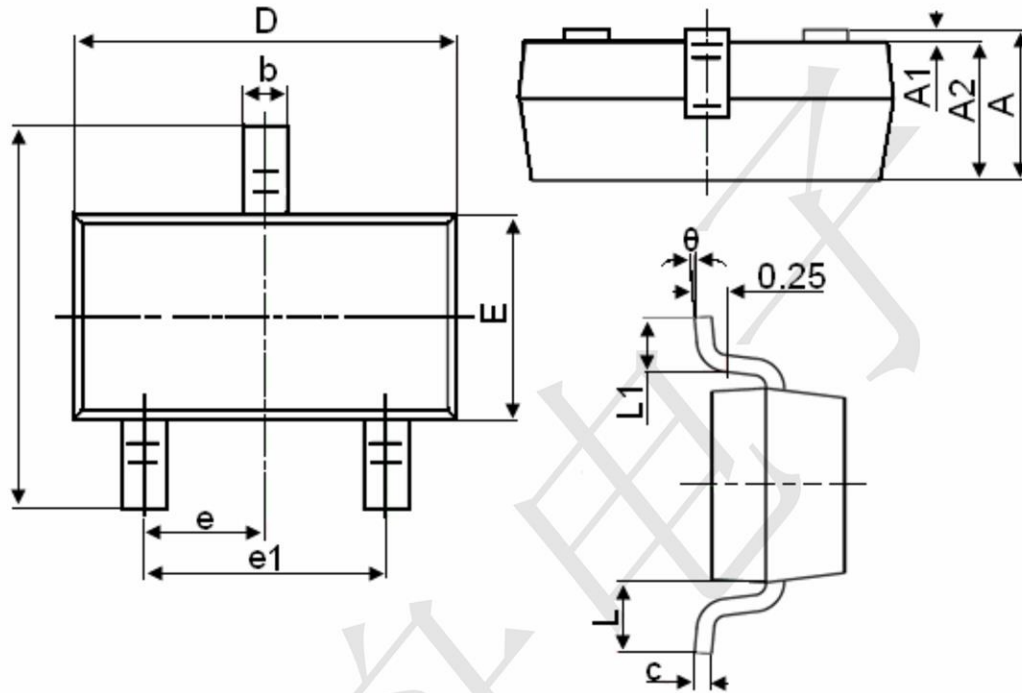
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	89.3	$^\circ C/W$
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Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$	-	-	± 10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.35	-0.65	-0.9	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-4A$	-	29	36	$m\Omega$
		$V_{GS}=-2.5V, I_D=-4A$	-	37	49	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-4A$	8	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V,$ $F=1.0MHz$	-	1181.1	-	PF
Output Capacitance	C_{oss}		-	121.3	-	PF
Reverse Transfer Capacitance	C_{rss}		-	114.8	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, R_L=2.5\Omega$ $V_{GS}=-4.5V, R_{GEN}=3\Omega$	-	12		nS
Turn-on Rise Time	t_r		-	10		nS
Turn-Off Delay Time	$t_{d(off)}$		-	19		nS
Turn-Off Fall Time	t_f		-	25		nS
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-4A,$ $V_{GS}=-4.5V$	-	10.2		nC
Gate-Source Charge	Q_{gs}		-	1.3	-	nC
Gate-Drain Charge	Q_{gd}		-	2.4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-4A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-4	A



SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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